## Minkyung Jung

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Circuit quantum electrodynamics with a spin qubit. Nature, 2012, 490, 380-383.	27.8	384
2	Field Tuning the <mml:math <br="" xmlns:mml="http://www.w3.org/1998/Math/MathML">display="inline"&gt;<mml:mi>g</mml:mi></mml:math> Factor in InAs Nanowire Double Quantum Dots. Physical Review Letters, 2011, 107, 176811.	7.8	135
3	Shell structures in self-assembled InAs quantum dots probed by lateral electron tunneling structures. Applied Physics Letters, 2005, 87, 203109.	3.3	58
4	Radio Frequency Charge Parity Meter. Physical Review Letters, 2012, 109, 166804.	7.8	56
5	Three Synthetic Routes to Single-Crystalline PbS Nanowires with Controlled Growth Direction and Their Electrical Transport Properties. ACS Nano, 2010, 4, 2391-2401.	14.6	50
6	A mechanical memory with a dc modulation of nonlinear resonance. Applied Physics Letters, 2010, 97, .	3.3	40
7	Radio frequency charge sensing in InAs nanowire double quantum dots. Applied Physics Letters, 2012, 100, .	3.3	38
8	GHz nanomechanical resonator in an ultraclean suspended graphene p–n junction. Nanoscale, 2019, 11, 4355-4361.	5.6	34
9	Transformation of ZnTe nanowires to CdTe nanowires through the formation of ZnCdTe–CdTe core–shell structure by vapor transport. Journal of Materials Chemistry, 2008, 18, 875.	6.7	30
10	Transport properties of single-crystalline n-type semiconducting PbTe nanowires. Nanotechnology, 2009, 20, 415204.	2.6	29
11	Quantum Interference in Radial Heterostructure Nanowires. Nano Letters, 2008, 8, 3189-3193.	9.1	26
12	Microwave Photodetection in an Ultraclean Suspended Bilayer Graphene p–n Junction. Nano Letters, 2016, 16, 6988-6993.	9.1	26
13	Reliable Multivalued Conductance States in TaO <sub><i>x</i> Sub&gt; Memristors through Oxygen Plasma-Assisted Electrode Deposition with in Situ-Biased Conductance State Transmission Electron Microscopy Analysis. ACS Applied Materials &amp; Interfaces, 2018, 10, 29757-29765.</sub>	8.0	26
14	Superconducting Junction of a Single-Crystalline Au Nanowire for an Ideal Josephson Device. ACS Nano, 2011, 5, 2271-2276.	14.6	24
15	Gigahertz Quantized Charge Pumping in Bottom-Gate-Defined InAs Nanowire Quantum Dots. Nano Letters, 2015, 15, 4585-4590.	9.1	22
16	Phase Controlled Growth of Cd <sub>3</sub> As <sub>2</sub> Nanowires and Their Negative Photoconductivity. Nano Letters, 2020, 20, 4939-4946.	9.1	20
17	Ultraclean Single, Double, and Triple Carbon Nanotube Quantum Dots with Recessed Re Bottom Gates. Nano Letters, 2013, 13, 4522-4526.	9.1	18
18	Impact of transient currents caused by alternating drain stress in oxide semiconductors. Scientific Reports, 2017, 7, 9782.	3.3	17

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19	Quantum Dots Formed in Three-dimensional Dirac Semimetal Cd <sub>3</sub> As <sub>2</sub> Nanowires. Nano Letters, 2018, 18, 1863-1868.	9.1	16
20	Measurement of Exciton and Trion Energies in Multistacked hBN/WS2 Coupled Quantum Wells for Resonant Tunneling Diodes. ACS Nano, 2020, 14, 16114-16121.	14.6	15
21	Short-channel effect and single-electron transport in individual indium oxide nanowires. Nanotechnology, 2007, 18, 435403.	2.6	13
22	Electrical breakdown and nanogap formation of indium oxide core/shell heterostructure nanowires. Nanotechnology, 2008, 19, 495702.	2.6	13
23	High-quality nanomechanical resonator based on a defect-free gold nanowire. Journal of the Korean Physical Society, 2013, 63, 263-268.	0.7	7
24	Controllable p–n junctions in three-dimensional Dirac semimetal Cd3As2 nanowires. Nanotechnology, 2020, 31, 205001.	2.6	4
25	Photocurrent response in few-layered ReS2 devices with short and open circuits. Journal of the Korean Physical Society, 2022, 80, 53-58.	0.7	3
26	Quantum interference effect in few-layered transition metal dichalcogenide. Current Applied Physics, 2020, 20, 451-455.	2.4	1
27	Polymorphic Ga <sub>2</sub> S <sub>3</sub> nanowires: phase-controlled growth and crystal structure calculations. Nanoscale Advances, 2022, 4, 3218-3225.	4.6	1